

In the Claims

Please amend the claims as follows:

1. (Currently Amended) A CPP spin-valve element formed on a substrate comprising:
 - a free layer structure including at least one ferromagnetic layer;
 - a pinned layer structure including at least one ferromagnetic layer and an anti-ferromagnetic layer set farther from the free layer structure than the ferromagnetic layer structure and rendering the pinned layer magnetically harder than the free layer;
 - a thin non-magnetic spacer layer structure configured to separate the free layer and the pinned layer structures, to prevent a direct exchange magnetic coupling between the free and pinned layer structures, and to allow an electric current to go there through; and
 - at least two current-confining (CC) layer structures including at least two parts having significantly different current conductivities;wherein each of said at least two CC layer structures is located on a different side of the thin non-magnetic spacer layer, and one of said two CC-layer structures is located in contact with said at least one ferromagnetic layer included in said free layer structure and the other CC-layer structure is located in contact with said at least one ferromagnetic layer included in said pinned layer structure, wherein none of the CC-layer structures are set in direct contact with said antiferromagnetic layer.
2. (Cancelled)
3. (Original) The CPP spin-valve element of claim 1, wherein said CC-layer structure includes a mosaic structure of conducting and insulating parts.

4. (Original) The CPP spin-valve element of claim 3, wherein said mosaic structure includes metal and oxide.

5. (Original) The CPP spin-valve element of claim 4, wherein said metal is selected from the group consisting of Ag, Al, Au, Co, Cr, Cu, Fe, Mg, Mn, Nb, Ni, Pd, Pt, Ta, Ti, V, Zr and their alloys and said oxide is selected from the group consisting of the oxides of Al, Co, Cr, Cu, Fe, Mg, Mn, Nb, Ni, Pd, Si, Ta, Ti, V, and Zr.

6. (Original) The CPP spin-valve element of claim 3, wherein said mosaic structure includes metal and nitride.

7. (Original) The CPP spin-valve element of claim 6, wherein said metal is selected from the group consisting of Ag, Al, Au, Co, Cr, Cu, Fe, Mn, Ni, Pd, Pt, Ta and their alloys and said nitride is selected from the group consisting of the nitrides of Al, B, C, Si, and Ta.

8. (Original) The spin-valve element of claim 1, wherein one of said CC-layer structures is located within or in the vicinity of said free layer structure and another of said CC-layer structures is located within or in the vicinity of said pinned layer structure.

9. (Withdrawn) The CPP spin-valve element of claim 1, wherein a bulk spin asymmetry coefficient, β , of a ferromagnetic layer of said ferromagnetic layer structures is greater than the interface spin asymmetry coefficient, γ , between a ferromagnetic layer of said ferromagnetic layer structures and a non-magnetic layer; and at least one of said CC-layer structures is located within the ferromagnetic layer of said ferromagnetic layer structure.

10. (Withdrawn) The CPP spin-valve element of claim 1, wherein an interface spin asymmetry coefficient, γ , of a ferromagnetic layer of said ferromagnetic layer structures and a non-magnetic layer is greater than a bulk spin asymmetry coefficient, β , of said ferromagnetic layer; and at least one of said CC-layer structures is located at or in the vicinity of the interface of either side of the ferromagnetic layer of said ferromagnetic layer structure.

11. (Withdrawn) The CPP spin-valve element of claim 1, wherein a bulk spin asymmetry coefficient, β , of both said free layer and pinned structures is greater than an interface spin asymmetry coefficient, γ ; and at least one of said CC-layer structures is located within the ferromagnetic layer of said free layer structure and at least another of said CC-layer structures is located within the ferromagnetic layer of said pinned layer structure.

12. (Withdrawn) The CPP spin-valve element of claim 1, wherein an interface spin asymmetry coefficient, γ , between each ferromagnetic layer of both said ferromagnetic layer structures is greater than a bulk spin asymmetry coefficient, β , and at least one of said CC-layer structures is located at or in the vicinity of the interface of either side of said free layer structure and at least another of said CC-layer structures is located at or in the vicinity of the interface of either side of said pinned layer.

13. (Currently Amended) The CPP spin-valve element of claim 1, wherein the width of at least one of the confined current paths of said CC-layer structures is greater than $t^{3/2}$ where t is the thickness measured in nano-meters of said ferromagnetic layers which include or lie next to said CC-layer structures.

14. (Previously Presented) The CPP spin-valve element of claim 1, wherein the width of the confined current paths of said CC-layer structures is greater than two times $t^{3/2}$ where t is the thickness measured in nano-meters of said ferromagnetic layers which include or lie next to said CC-layer structures.

15. (Original) The CPP spin-valve element of claim 1, wherein at least one confined-current path is formed within every flux path of a width of an exchange length of the free layer except at side edges of the free layer.

16. (Original) The CPP spin-valve element of claim 1, wherein a pair of CC-layer structures are located on both sides across said free layer structure or said pinned layer whose conducting parts are located in a cascade manner, and at least the inner edge to edge distance of a projection of the conducting parts of the CC-layers forming at least one of the current paths through at least one of said free layer structure and said pinned layer onto the layer plane is made greater than the thickness of at least one of said free layer structure and said pinned layer.

17. (Original) The CPP spin-valve element of claim 1, wherein a pair of CC-layer structures are located on both sides across said free layer structure or said pinned layer whose conducting parts are located in a cascade manner, and the length of at least one of the current paths through at least one of said free layer structure and said pinned layer structure is greater than a half of a spin diffusion length in at least one of said free layer structure and said pinned layer structure and is smaller than 3 times as large as a spin diffusion length.

18. (Original) The CPP spin-valve element of claim 17, wherein said length of at least one of the current paths through at least one of said free layer structure and said pinned layer structure is greater than the spin diffusion length in at least one of said free layer structure and said pinned layer structure and is smaller than 2 times as large as the spin diffusion length of said current paths.

19. (Currently Amended) A CPP spin-valve element formed on a substrate comprising:

a free layer structure including at least one ferromagnetic layer;

a pinned layer structure including at least one ferromagnetic layer, the free layer is magnetically softer than the pinned layer; and

a thin non-magnetic current confining (CC)-layer structure configured to separate the free and pinned layers, to prevent a substantial magnetic coupling between said free and pinned layer structures, and to allow an electric current to go through the confined current paths;

wherein the width of at least one of the confined current paths of said CC-layer structure is greater than $t^{3/2}$ where t is the thickness of at least one of said free layer structure and said pinned layer measured in nano-meters.

20. (Previously Presented) The CPP spin-valve element of claim 19, wherein the width of the confined current paths of said CC-layer structure is greater than two times $t^{3/2}$ where t is the thickness of at least one of said free layer structure and pinned layer measured in nano-meters.

21. (Currently Amended) A CPP spin-valve element formed on a substrate comprising:

a free layer structure including at least one ferromagnetic layer;

a pinned layer structure including at least one ferromagnetic layer, the free layer is magnetically softer than the pinned layer; and

a first thin non-magnetic current confining (CC)-layer structure configured to separate the free and pinned layers, to prevent a substantial magnetic coupling between said free and pinned layer structures, and to allow an electric current to go through the confined current paths; and

a second CC-layer structure placed across at least one of the free layer and the pinned layer;

wherein conducting parts of said CC-layers are located in a cascade manner and at ~~least an a majority of the nearest~~ inner edge to edge ~~distance~~ distances of a projection of the conducting parts of the CC-layers forming ~~at least one of~~ the current paths through said free layer structure or said pinned layer onto the layer plane ~~[[is]]~~ are made greater than the thickness of at least one of said free layer ~~structure~~ and said pinned layer.

22. (Cancelled)

23. (Previously Presented) The CPP spin-valve element of claim 21, wherein the width of the confined current paths of said first and second CC-layer structures is greater than $t^{3/2}$ where t is the thickness of at least one of said free layer structure and said pinned layer measured in nano-meters.

24. (Previously Presented) The CPP spin-valve element of claim 21, wherein the width of the confined current paths of said first and second CC-layer structures is greater than two times $t^{3/2}$ where t is the thickness of at least one of said free layer structure and said pinned layer measured in nano-meters.

25. (Cancelled)

26. (Previously Presented) The CPP spin-valve element of claim 21, wherein the length of at least one of the current paths through at least one of said free layer structure and said pinned layer structure is greater than a half of a spin diffusion length in at least one of said free layer structure and said pinned layer and is smaller than 3 times as large as the spin diffusion length.

27. (Original) The CPP spin-valve element of claim 26, wherein the length of at least one of the current paths through at least one of said free layer structure and said pinned layer structure is greater than a spin diffusion length in at least one of said free layer structure and said pinned layer and is smaller than 2 times as large as the spin diffusion length.

28. (Currently Amended) A CPP spin-valve element formed on a substrate comprising:

a free layer structure including at least one ferromagnetic layer; and

a pinned layer structure including at least one ferromagnetic layer, the free layer is magnetically softer than the pinned layer;

wherein at least one CC-layer structure is incorporated therein, which is configured to separate the free and pinned layers and to allow an electric current to go through the confined

current paths, the width of at least one of the confined current paths of said at least one CC-layer structure is greater than $t^{3/2}$ where t is the thickness of at least one of said free layer structure and pinned layer measured in nano-meters.

29. (Previously Presented) The CPP spin-valve element of claim 28, wherein the width of at least one of the confined current paths of said CC-layer structure is greater than two times $t^{3/2}$ where t is the thickness of at least one of said free layer structure and pinned layer measured in nano-meters.

30. (Withdrawn) A CPP spin-valve element formed on a substrate comprising:
a free layer structure including at least one ferromagnetic layer;
a pinned layer structure including at least one ferromagnetic layer, the free layer is magnetically softer than the pinned layer;
a thin non-magnetic current confining (CC)-layer structure configured to separate the free and pinned layers, to prevent a substantial magnetic coupling between said free and pinned layer structures, and to allow an electric current to go through the confined current paths; and
lead layers configured to be connected to electrodes;
wherein at least said non-magnetic layer and said pinned layer structure are formed in a CC-layer structure forming at least one confined current path.

31. (Withdrawn) The CPP spin-valve element of claim 30, wherein the width of at least one of the confined current paths of said CC-layer structure is greater than the power of 1.5 of the thickness of said free layer structure measured in nano-meters.

32. (Withdrawn) The CPP spin-valve element of claim 30, wherein the width of at least one of the confined current paths of said CC-layer structure is greater than two times the power of 1.5 of the thickness of said free layer structure.

33. (Withdrawn) The spin-valve element of claim 30, wherein at least another CC-layer structure is incorporated across the free layer structure.

34. (Withdrawn) The spin-valve element of claim 33, wherein at least said another CC-layer structure is incorporated across the free layer structure, the width of at least one of the confined current paths of said CC-layer structure is greater than the power of 1.5 of the thickness of said free layer structure measured in nano-meters.

35. (Withdrawn) The CPP spin-valve element of claim 33, wherein the width of at least one of the confined current paths of said CC-layer structure is greater than two times the power of 1.5 of the thickness of said free layer structure measured in nano-meters.

36. (Withdrawn) The CPP spin-valve element of claim 33, wherein conducting parts of the CC-layers facing across said free layer structure are located in a cascade manner, and a projection of the length of at least one of the current paths through said free layer structure onto the layer plane is made greater than the thickness of said free layer structure.

37. (Withdrawn) The CPP spin-valve element of claim 33, wherein said length of at least one of the current paths through said free layer structure is greater than a half of a spin diffusion length in said free layer structure or said pinned layer structure and smaller than 3 times as large as the spin diffusion length.

38. (Withdrawn) The CPP spin-valve element of claim 37, wherein said length of at least one of the current paths through said free layer structure is greater than the spin diffusion length in said free layer structure and smaller than 2 times as large as the spin diffusion length.

39. (Previously Presented) The CPP spin-valve element of claim 1, wherein said CC-layer structures are fabricated with a lithography technique using a focused ion beam or an electrochemical scanning probe.

40. (New) A CPP spin-valve element formed on a substrate comprising:
a free layer structure including at least one ferromagnetic layer;
a pinned layer structure including at least one ferromagnetic layer;
a thin non-magnetic spacer layer structure configured to separate the free layer and the pinned layer structures, to prevent a direct exchange magnetic coupling between the free and pinned layer structures, and to allow an electric current to go there through; and
at least two CC-layer structures including at least two parts having significantly different current conductivities;

wherein a pair of said at least two CC-layer structures are separated by the thin non-magnetic spacer layer, at least one of said at least two CC-layer structures is inserted within the at least one ferromagnetic layer of the pinned layer structure, and the part of the CC-layer structures having a lower conductivity includes either a ferromagnetic or ferrimagnetic material.

41 (New). A CPP spin-valve element formed on a substrate comprising:

a free layer structure including at least one ferromagnetic layer;
a pinned layer structure including at least one ferromagnetic layer;
a thin non-magnetic spacer layer structure configured to separate the free layer and the pinned layer structures, to prevent a direct exchange magnetic coupling between the free and pinned layer structures, and to allow an electric current to go there through; and

at least two CC-layer structures including at least two parts having significantly different current conductivities;

wherein a pair of said at least two CC-layer structures are separated by the thin non-magnetic spacer layer, at least one of said at least two CC-layer structures is inserted within the at least one ferromagnetic layer of the pinned layer structure or the free layer structure, the part of the CC-layer structures having a higher conductivity includes either a ferromagnetic or a ferromagnetic material.

42. (New) The CPP spin-valve element of claim 19, wherein the average width of the confined current paths of said CC-layer structure is greater than $2.5t^{3/2}$ where t is the thickness of at least one of said free layer structure and said pinned layer measured in nano-meters.

43. (New) The CPP spin-valve element of claim 13, wherein the average width of the confined current paths of said CC-layer structures is greater than $t^{3/2}$ where t is the thickness measured in nano-meters of said ferromagnetic layers which include or lie next to said CC-layer structures.

44. (New) The CPP spin-valve element of claim 19, wherein the average width of the confined current paths of said CC-layer structure is greater than $t^{3/2}$ where t is the

thickness of at least one of said free layer structure and said pinned layer measured in nano-meters.

45. (New) The CPP spin-valve element of claim 28, wherein the average width of the confined current paths of said CC-layer structure is greater than $t^{3/2}$ where t is the thickness of at least one of said free layer structure and said pinned layer measured in nano-meters.

46. (New) The CPP spin-valve element of claim 29, wherein the average width of the confined current paths of said CC-layer structure is greater than two times $t^{3/2}$ where t is the thickness of at least one of said free layer structure and pinned layer measured in nano-meters.